

## Sub-stoichiometric WO<sub>2.9</sub> for formaldehyde sensing and treatment: a first principles study

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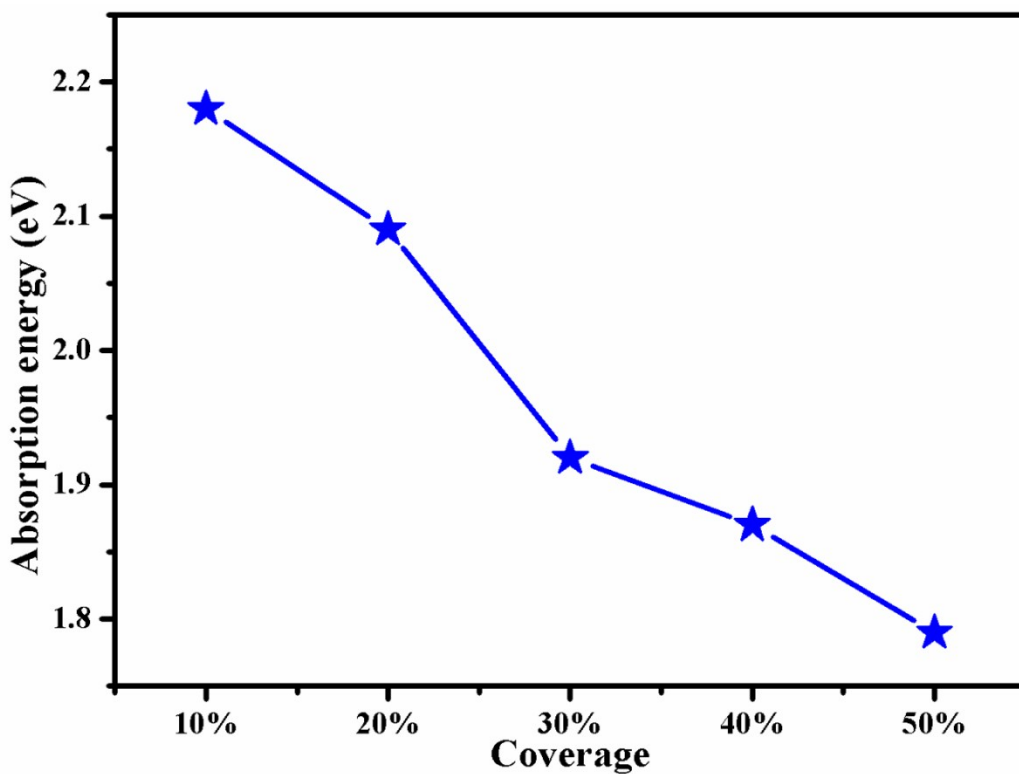
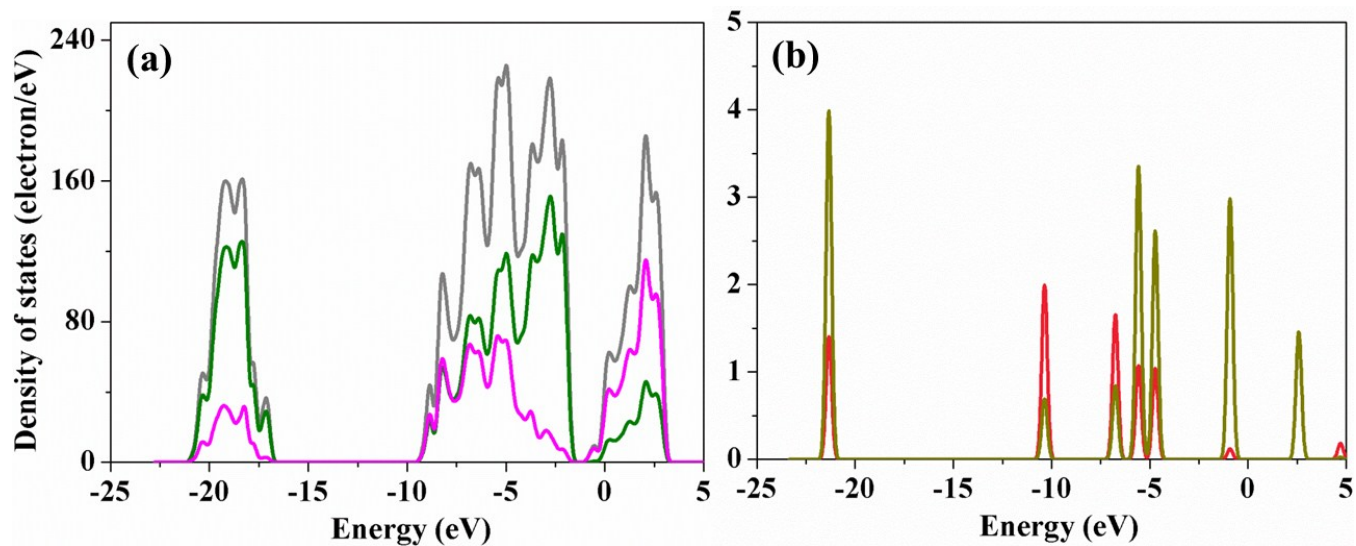
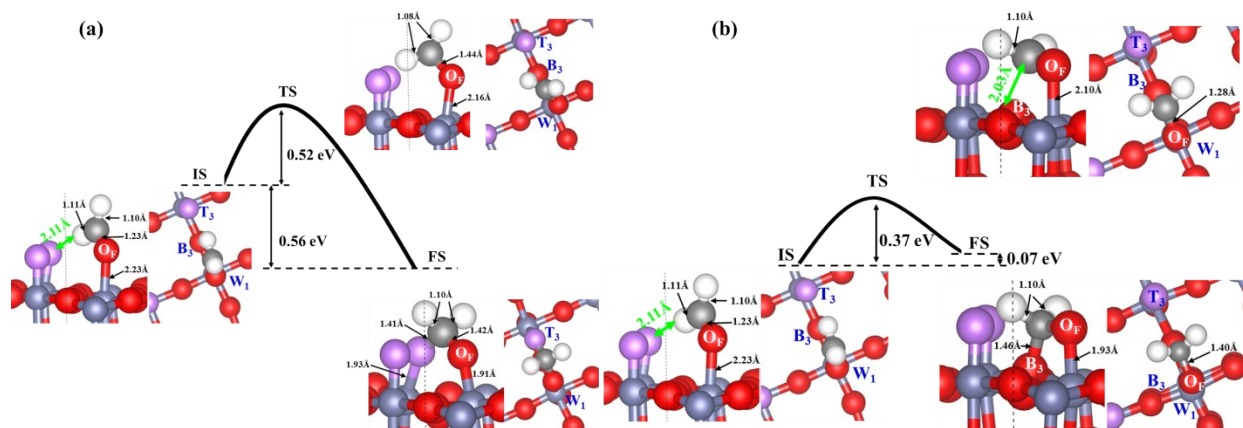


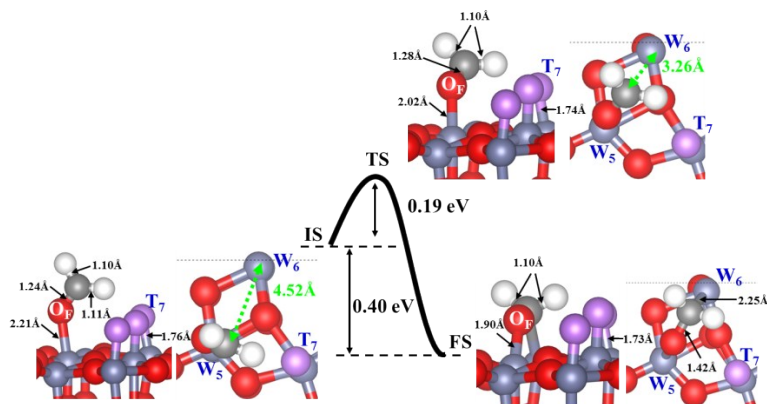
Figure S1. Coverage-dependent absorption energies of HCHO on WO<sub>2.9</sub> (010) surface in configurations of type I.



**Figure S2.** (a) The total density of states (TDOS) for  $\text{WO}_{2.9}$  (010) surface (Gray curve) and DOS projected on the O atoms (Olive curve) and on the W atoms (Pink curve); (b) DOS projected (PDOS) on the  $\text{C}_F$  atom of HCHO molecule (Magenta curve) and on the  $\text{O}_F$  atom of HCHO molecule (Dark yellow curve). The Fermi level of  $\text{WO}_{2.9}$  (010) surface is assigned at 0 eV.



**Figure S3.** The barriers and the corresponding transition states of (a) the Type I and (b) the type III adsorption configurations transformed from type IV.



**Figure S4.** The minimum energy path for HCHO absorption configuration transform from type IV to type II.